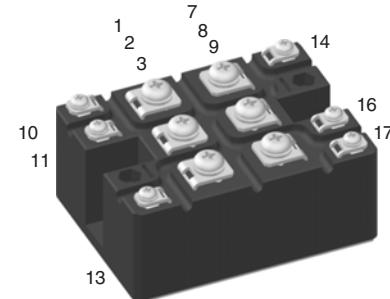
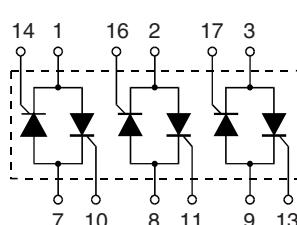


Three Phase AC Controller Modules

I_{RMS} = 40 A
V_{RRM} = 1200-1600 V

Preliminary data

V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V	V	
1200	1200	VWO 40-12io7
1400	1400	VWO 40-14io7
1600	1600	VWO 40-16io7



Symbol	Conditions	Maximum Ratings		
I _{RMS}	T _C = 85°C, 50 - 400 Hz (per phase)	40	A	
I _{TRMS}	T _{VJ} = T _{VJM}	29	A	
I _{TAVM}	T _C = 85°C; (180° sine)	18	A	
I _{TSM}	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	400 450	A A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	360 390	A A
I ² t	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	800 850	A ² s A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	650 640	A ² s A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.3 A di _G /dt = 0.3 A/µs	repetitive, I _T = 150 A non repetitive, I _T = I _{TAVM}	100 500	A/µs A/µs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GR} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/µs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 µs t _p = 300 µs	10 5	W W
P _{GAVM}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	2500 3000	V~
M _d	Mounting torque (M5) Terminal connection torque (M3; M5)		5/44±15% Nm/lb.in. 1.5/13±15% Nm/lb.in.	
Weight	typ.		180	g

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.

Symbol	Conditions	Characteristic Values			
I_D, I_R	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$	\leq	5	mA	
V_T	$I_T = 80 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	\leq	1.65	V	
V_{T0}	For power-loss calculations only		0.85	V	
r_T			15	$\text{m}\Omega$	
V_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	\leq	1.0	V
		$T_{VJ} = -40^\circ\text{C}$	\leq	1.6	V
I_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	\leq	100	mA
		$T_{VJ} = -40^\circ\text{C}$	\leq	150	mA
V_{GD}	$T_{VJ} = T_{VJM}$	$V_D = \frac{2}{3} V_{DRM}$	\leq	0.2	V
I_{GD}			\leq	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}$; $t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}$; $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	200	mA	
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$	\leq	150	mA	
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 \text{ A}$; $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	2	μs	
t_q	$T_{VJ} = T_{VJM}$; $I_T = 20 \text{ A}$, $t_p = 200 \mu\text{s}$; $di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$; $dv/dt = 15 \text{ V}/\mu\text{s}$; $V_D = \frac{2}{3} V_{DRM}$	typ.	150	μs	
$R_{th,JC}$	per thyristor; sine 180°el		1.43	K/W	
	per module		0.238	K/W	
$R_{th,JK}$	per thyristor; sine 180°el		1.53	K/W	
	per module		0.255	K/W	
d_s	Creeping distance on surface		8.0	mm	
d_A	Creepage distance in air		4.5	mm	
a	Max. allowable acceleration		50	m/s^2	

